

WHAT IS CLAIMED IS:

1. A semiconductor device comprising:

a first semiconductor layer formed in a first region of a semiconductor substrate with one of an insulating film and a cavity interposed between said semiconductor substrate and said first semiconductor layer; and

a plurality of second semiconductor layers formed in second regions of said semiconductor substrate.

10 2. A semiconductor device according to claim 1, wherein at least a portion of said plurality of second semiconductor layers is formed within the range of a radius of 5 mm from a certain point on said first semiconductor layer.

15 3. A semiconductor device according to claim 1, wherein each of said plurality of second semiconductor layers is surrounded by said first semiconductor layer.

20 4. A semiconductor device according to claim 1, wherein a logic circuit is formed in said first semiconductor layer, and at least one of a storage element, analog element, and signal input/output circuit is formed in said plurality of second semiconductor layers.

25 5. A semiconductor device according to claim 1, wherein one of said plurality of second semiconductor layers surrounds said first semiconductor layer.

6. A semiconductor device according to claim 1,

wherein said plurality of second semiconductor layers are arranged to be symmetrical with respect to a certain point on said semiconductor substrate.

7. A semiconductor device according to claim 1,
5 wherein said plurality of second semiconductor layers are arranged to be symmetrical with respect to a certain straight line on said semiconductor substrate.

8. A semiconductor device in which a plurality of semiconductor devices according to claim 1 are laid
10 out.

9. A semiconductor device according to claim 1,
wherein one of said plurality of second semiconductor layers is formed on an outerperipheral of said semiconductor substrate.

15 10. A semiconductor device in which a plurality of semiconductor devices according to claim 9 are laid out.

11. A semiconductor device according to claim 1,
20 wherein the sum of the areas of said plurality of second semiconductor layers is larger than the area of said first semiconductor layer.

12. A semiconductor device according to claim 1,
wherein said plurality of second semiconductor layers are deposited by epitaxial growth.

25 13. A semiconductor device comprising:
a plurality of first semiconductor layers formed in a first region of a semiconductor substrate with one

of an insulating film and a cavity interposed between said semiconductor substrate and said plurality of first semiconductor layers; and

5 a second semiconductor layer formed in a second region of said semiconductor substrate.

14. A semiconductor device according to claim 13, wherein at least a portion of said second semiconductor layer is formed within the range of a radius of 5 mm from a certain point on said plurality of first
10 semiconductor layers.

15. A semiconductor device according to claim 13, wherein each of said plurality of first semiconductor layers is surrounded by said second semiconductor layer.

15 16. A semiconductor device according to claim 13, wherein logic circuits are formed in said plurality of first semiconductor layers, and at least one of a storage element, analog element, and signal input/output circuit is formed in said second
20 semiconductor layer.

17. A semiconductor device according to claim 13, wherein said plurality of first semiconductor layers are arranged to be symmetrical with respect to a certain point on said semiconductor substrate.

25 18. A semiconductor device according to claim 13, wherein said plurality of first semiconductor layers are arranged to be symmetrical with respect to a

certain straight line on said semiconductor substrate.

19. A semiconductor device according to claim 13,
wherein the area of said second semiconductor layer is
larger than the sum of the areas of said plurality of
5 first semiconductor layers.

20. A semiconductor device according to claim 13,
wherein said second semiconductor layer is deposited by
epitaxial growth.

21. A semiconductor device comprising:
10 a first semiconductor layer formed on a
semiconductor substrate with one of an insulating film
and a cavity interposed between said semiconductor
substrate and said first semiconductor layer, said
first semiconductor layer being a rectangle; and

15 a second semiconductor layer formed on an
outerperipheral of said semiconductor substrate, said
second semiconductor layer surrounding said first
semiconductor layer, said second semiconductor layer
extending to a corner of said first semiconductor
layer.

22. A semiconductor device according to claim 21,
wherein the area of said second semiconductor layer is
larger than the area of said first semiconductor layer.

23. A semiconductor device according to claim 21,
25 wherein said second semiconductor layer is deposited by
epitaxial growth.

24. A semiconductor device comprising:

a first semiconductor layer formed in a first region of a semiconductor substrate with an insulating film interposed between said semiconductor substrate and said first semiconductor layer; and

- 5 a second semiconductor layer formed in a second region of said semiconductor substrate, at least a portion of said second semiconductor layer being formed within the range of a radius of 5 mm from any point on said first semiconductor layer.